

Electronic Supplementary Information (ESI)

Enhanced Electrocatalytic Performance of Graphene Counter Electrode *via* Incorporation of SiO₂ Nanoparticles for Dye-Sensitized Solar Cells

Feng Gong, Zhuoqun Li, Hong Wang and Zhong-Sheng Wang*

Department of Chemistry & Lab of Advanced Materials, Fudan University, 2205
Songhu Road, Shanghai 200438, PR China.

* Corresponding author: E-mail: zs.wang@fudan.edu.cn, Fax/Tel: +86-21-5163-0345

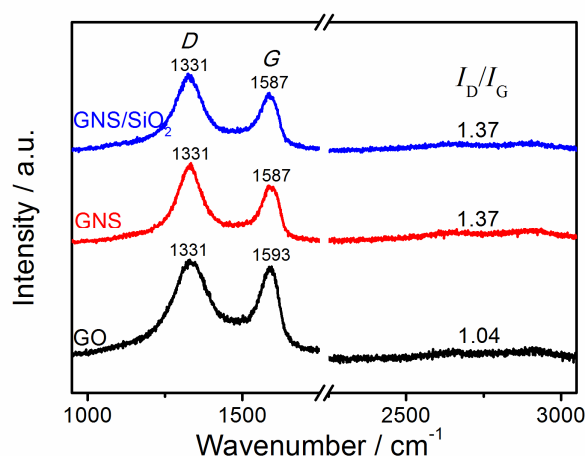


Fig. S1 Raman spectra for GO, GNS and GNS/SiO₂ products

Fig. S1 depicts the typical Raman spectra of GO, GNS and GNS/SiO₂. The spectrum for GO shows two prominent bands located at 1593 cm⁻¹ (G band) and 1331 cm⁻¹ (D band), which are usually assigned to zone center phonons of E_{2g} symmetry and K -point phonons of A_{1g} symmetry, respectively.¹ Thus, the intensity ratio of the D and G band (I_D/I_G) is usually taken as an indication of the relative disorder present in graphitic structures. The spectrum for GNS displays G and D bands at 1587 and 1331 cm⁻¹, respectively. The G band shifts from 1593 to 1587 cm⁻¹, which confirms the reduction of GO to GNS during the chemical treatment.² Furthermore, the I_D/I_G varies from 1.04 for GO to 1.37 for GNS. This change suggests a decrease in the average size of the sp² domains upon reduction of the exfoliated GO.³ For the GNS/SiO₂ composite, the position and intensity of D band and G band have scarcely changed upon incorporation of SiO₂, indicating a physical adsorption mode on GNS. It has

been reported that silica, when noncovalently attached to carbon nanotubes, did not influence the band position and intensity ratio of D band to G band.⁴

References

1. A. C. Ferrari and J. Robertson, *Phys. Rev. B*, 2000, **61**, 14095.
2. W. Chen, L. Yan and P. R. Bangal, *J. Phys. Chem. C*, 2010, **114**, 19885.
3. S. Stankovich, D. A. Dikin, R. D. Piner, K. A. Kohlhaas, A. Kleinhammes, Y. Jia, Y. Wu, S. T. Nguyen and R. S. Ruoff, *Carbon*, 2007, **45**, 1558.
4. L. Kou and C. Gao, *Nanoscale*, 2011, **3**, 519.